

# BT1308 series D

Triacs logic level
Rev. 01 — 26 February 2008

**Product data sheet** 

### **Product profile**

### 1.1 General description

Passivated sensitive gate triacs in a SOT54 plastic package

#### 1.2 Features

- Sensitive gate
- Direct interfacing to logic level ICs
- Gate triggering in four quadrants
- Direct interfacing to low-power gate drive circuits

### 1.3 Applications

- General purpose switching and phase control
- Low-power AC fan speed control

#### 1.4 Quick reference data

- $V_{DRM} \le 400 \text{ V (BT1308-400D)}$
- $V_{DRM} \le 600 \text{ V (BT1308-600D)}$
- $I_{TSM} \le 9 \text{ A (t = 20 ms)}$

- $I_{GT} \le 5 \text{ mA}$
- $I_{GT} \le 7 \text{ mA } (T2-G+)$
- $I_{T(RMS)} \le 0.8 A$

# **Pinning information**

Table 1. Pinning

Di-	Decembries	Cimpulified cutting	Orankia ayımlad
Pin	Description	Simplified outline	Graphic symbol
1	main terminal 2 (T2)		N.1
2	gate (G)		T2T1
3	main terminal 1 (T1)		`G sym051
		SOT54 (TO-92)	



# 3. Ordering information

### Table 2. Ordering information

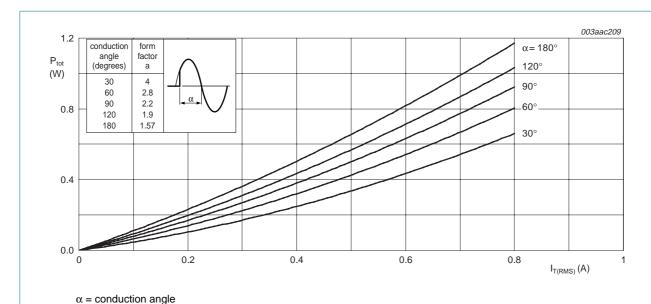
Type number	Package		
	Name	Description	Version
BT1308-400D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54
BT1308-600D			

# 4. Limiting values

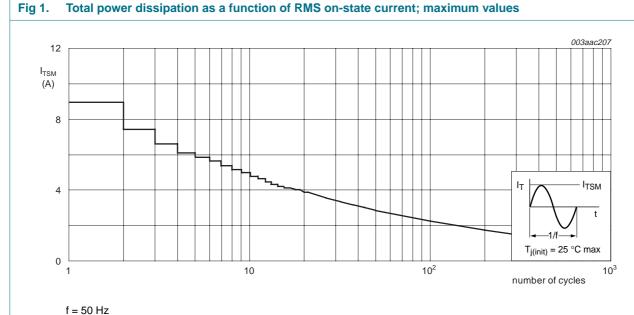
### Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

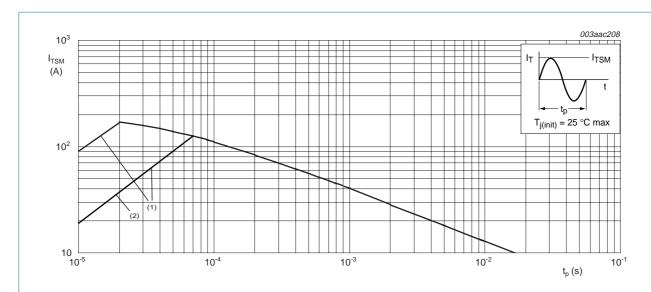
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage	BT1308-400D	-	400	V
		BT1308-600D	-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{lead} \le 55$ °C; see Figure 4 and 5	-	8.0	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3			
		t = 20 ms	-	9	Α
		t = 16.7 ms	-	10	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms	-	0.32	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_{TM}$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 0.2 A/ $\mu s$			
		T2+ G+	-	50	A/μs
		T2+ G-	-	50	A/μs
		T2- G-	-	50	A/μs
		T2- G+	-	10	A/μs
$I_{GM}$	peak gate current		-	1	Α
$P_GM$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
$T_{stg}$	storage temperature		-40	+150	°C
T <sub>j</sub>	junction temperature		-	125	°C



Total power dissipation as a function of RMS on-state current; maximum values



Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum Fig 2. values



 $t_p \le 20 \text{ ms}$ 

- (1) dI<sub>T</sub>/dt limit
- (2) T2- G+ quadrant limit

Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values

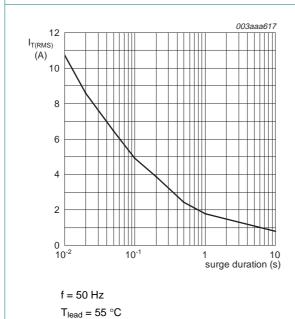


Fig 4. RMS on-state current as a function of surge duration; maximum values

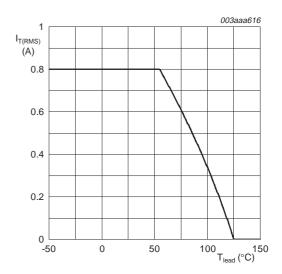
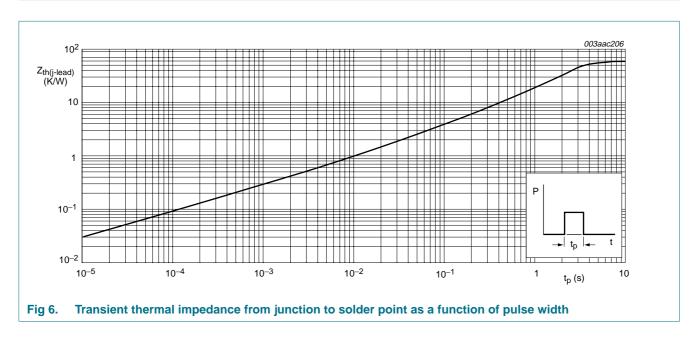


Fig 5. RMS on-state current as a function of lead temperature; maximum values

### 5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-lead})}$	thermal resistance from junction to lead	full cycle	-	-	60	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	full cycle; printed-circuit board mounted; lead length 4 mm; see Figure 6	-	150	-	K/W

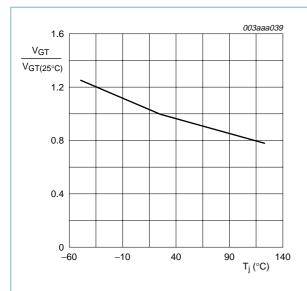


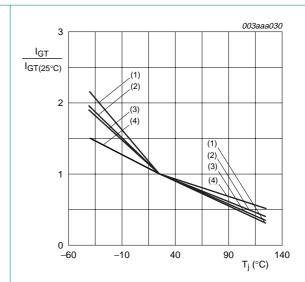
### 6. Characteristics

Table 5. Characteristics

 $T_j = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; see <u>Figure 8</u>				
		T2+ G+	-	1	5	mΑ
		T2+ G-	-	2	5	mΑ
		T2- G-	-	2	5	mΑ
		T2- G+	-	4	7	mΑ
IL	latching current	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; see } \frac{\text{Figure 10}}{\text{ of } 100000000000000000000000000000000000$				
		T2+ G+	-	1	10	mΑ
		T2+ G-	-	5	10	mΑ
		T2- G-	-	1	10	mΑ
		T2- G+	-	2	10	mΑ
I <sub>H</sub>	holding current	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; see } \frac{\text{Figure 11}}{\text{Figure 11}}$	-	1	10	mΑ
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 0.85 A; see <u>Figure 9</u>	-	1.35	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; see } Figure 7$	-	0.9	2	V
		$V_D = V_{DRM}; I_T = 0.1 A; T_j = 110 ^{\circ}C$	0.1	0.7	-	V
I <sub>D</sub>	off-state current	$V_D = V_{DRM(max)}$ ; $T_j = 125  ^{\circ}C$	-	0.1	0.5	mΑ
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)}; T_j = 110  ^{\circ}C;$ exponential waveform; gate open circuit	30	45	-	V/μs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_{DM} = V_{DRM(max)}$ ; $T_j = 50$ °C; $I_{TM} = 0.84$ A; $dI_{com}/dt = 0.3$ A/ms	-	5	-	V/μs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 1 \text{ A}; V_D = V_{DRM(max)}; I_G = 25 \text{ mA}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

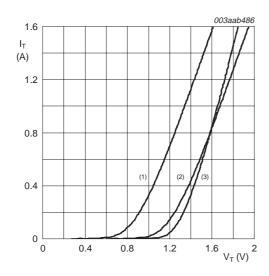




- (1) T2+ G+
- (2) T2-G+
- (3) T2-G-
- (4) T2+ G-

Fig 7. Normalized gate trigger voltage as a function of junction temperature





 $V_0 = 1.171 \ V$ 

 $R_s = 0.5125 \Omega$ 

- (1)  $T_i = 125$  °C; typical values
- (2)  $T_i = 125 \,^{\circ}C$ ; maximum values
- (3)  $T_j = 25 \,^{\circ}C$ ; maximum values

Fig 9. On-state current as a function of on-state voltage

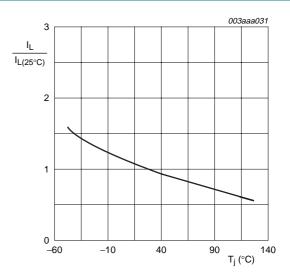
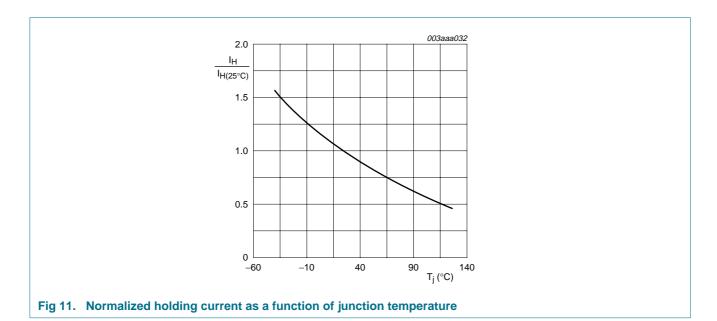


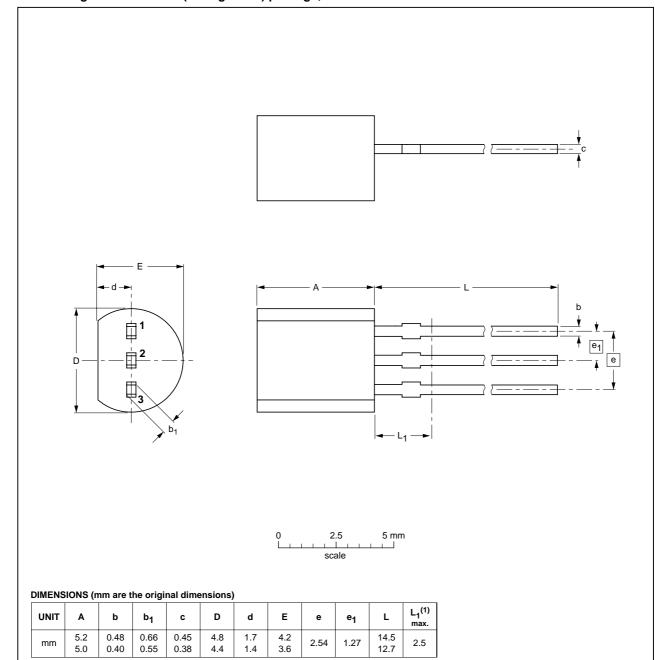
Fig 10. Normalized latching current as a function of junction temperature



# 7. Package outline

#### Plastic single-ended leaded (through hole) package; 3 leads

SOT54



#### Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEDEC JEITA	PROJECTION	ISSUE DATE	
SOT54		TO-92	SC-43A		<del>-04-06-28-</del> 04-11-16	

Fig 12. Package outline SOT54 (TO-92)

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# 8. Revision history

### Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BT1308_SER_D_1	20080226	Product data sheet	-	-

### 9. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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# BT1308 series D

**Triacs logic level** 

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